Photocouplers Infrared LED & Photo IC

TLP5214A

±4.0 A (max)

15 V to 30 V

6 mA (max)

150 ns (max)

1.1 μs (typ.)

±35 kV/µs (min)

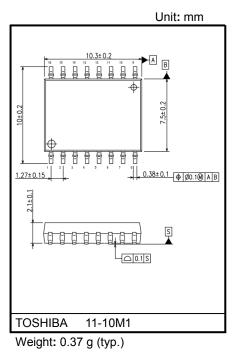
5000 Vrms (min)

Isolated IGBT/Power MOSFET gate drive AC and brushless DC motor drives Industrial Inverters and Uninterruptible Power Supply (UPS)

The TLP5214A is a highly integrated 4.0 A output current IGBT gate drive photocoupler housed in a long creepage and clearance SO16L package. The TLP5214A, a smart gate driver photocoupler, includes functions of IGBT desaturation detection, isolated fault status feedback, soft IGBT turn-off, active Miller cramping and under voltage lockout (UVLO). Moreover, this phorocoupler has features of the desaturation leading edge blanking time, filtering time, and optimisation of the soft-shutdown performance for secure operation of applications. This photocoupler is suitable for driving IGBT and power MOSFET used in inverter applications.

The TLP5214A consists two infrared LEDs and two high-gain and high-speed ICs. They realize high current, high-speed output control and output fault status feedback.

- Peak output current:
- Guaranteed performance over temperature: -40 to 110 °C
- Supply current: 3.8 mA (max)
- Power supply voltage:
- Threshold input current:
- Propagation delay time:
- DESAT leading edge blanking time:
- Common-mode transient immunity:
- Isolation voltage:
- UL-recognized : UL 1577, File No.E67349
- cUL-recognized :CSA Component Acceptance Service No. 5A, File No.E67349
- VDE approved: EN 60747-5-5, EN 62368-1 (Note 1)



Construction mechanical rating

	SO16L
Height Creepage Distance Clearance Insulation Thickness	2.3 mm (max) 8.0 mm (min) 8.0 mm (min) 0.4 mm (min)

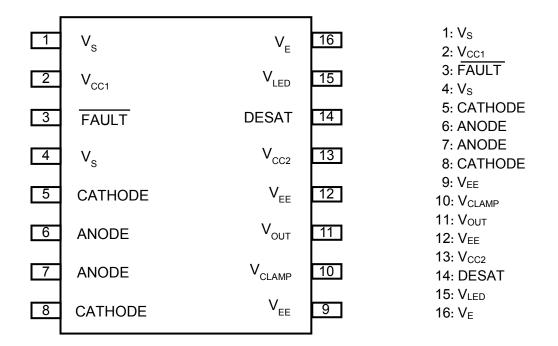
Note 1: When a VDE approved type is needed, please designate the Option(D4).

Truth Table

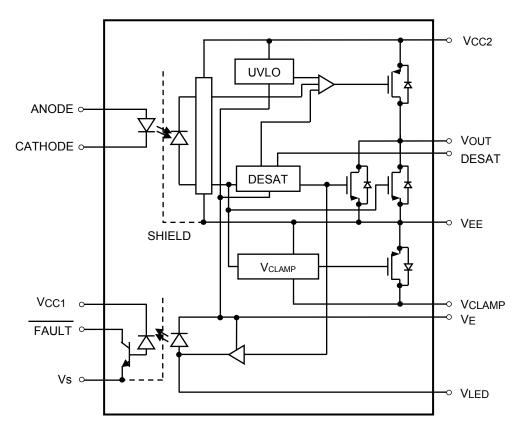
IF	UVLO	DESAT	FAULT	Va	
IF	(Vcc2-VE)	(14Pin DESAT Terminal Input)	(3Pin FAULT Terminal Output)	Vo	
OFF	Not Active (> VUVLO ⁺)	Not Active	High	Low	
ON	Not Active (> V _{UVLO} ⁺)	Low (< V _{DESATth})	High	High	
ON	Not Active (> VUVLO ⁺)	High (> VDESATth)	Low (FAULT)	Low	
ON	Active (< Vuv∟o⁻)	Not Active	High	Low	
OFF	Active (< Vuv∟o⁻)	Not Active	High	Low	

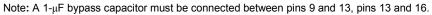
Start of commercial production 2017-03

Pin Configuration (top view)



Internal Circuit





Absolute Maximum Ratings (Note) (Unless otherwise specified, Ta = 25 °C)

	Characteristic	S	Symbol	Rating	Unit
LED	Input forward current		lF	25	mA
	Input forward current derating (Ta ≥	95°C)	∆l _F /∆Ta	-1	mA/°C
	Peak transient input forward current	(Note 1)	IFPT	1	A
	Peak transient input forward current of	lerating (Ta ≥ 95°C)	ΔIFPT/ΔTa	-25	mA/°C
	Reverse input voltage		VR	6	V
	Input power dissipation		PD	145	mW
	Input power dissipation derating (Ta	≥ 95°C)	$\Delta P_D / \Delta Ta$	-5.0	mW/°C
Detector	Positive input supply voltage		Vcc1	-0.5 to 7	V
	"H" peak output current	Ta = -40 to 110 °C	Іорн	-4.0	А
	"L" peak output current	(Note 2)	IOPL	+4.0	А
	FAULT output current		IFAULT	8	mA
	FAULT pin voltage		VFAULT	-0.5 to Vcc1	V
	Total output supply voltage		(VCC2-VEE)	-0.5 to 35	V
	Negative output supply voltage		(VE-VEE)	-0.5 to 15	V
	Positive output supply voltage		(VCC2-VE)	-0.5 to 35 - (VE-VEE)	V
	Output voltage		Vo	-0.5 to Vcc2	V
	Peak clamping sinking current		IClamp	1.7	А
	Miller clamping pin voltage		VClamp	-0.5 to Vcc2	V
	DESAT voltage		VDESAT	V_E to V_E + 10	V
	Output power dissipation		Po	410	mW
	Output power dissipation derating (Ta	l ≥ 95°C)	Δ P _O /ΔTa	-14.0	mW/°C
Common	Operating temperature range		Topr	-40 to 110	°C
	Storage temperature range		Tstg	-55 to 125	°C
	Lead soldering temperature (10 s)	Tsol	260	°C	
	Isolation voltage (AC, 60 s, R.H. ≤ 60	%) (Note 4)	BVS	5000	Vrms

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

- Note: A ceramic capacitor (1 μ F) should be connected between pins 9 and 13, pins 13 and 16 to stabilize the operation of the high gain linear amplifier. Furthermore, in case V_E V_{EE} > 0 V, a bypass capacitor, which has good high frequency characteristic, a ceramic capacitor (1 μ F) should be connected between pins 9 and 16. Failure to provide the bypassing may impair the switching property. The total lead length between capacitor and coupler should not exceed 1 cm.
- Note 1: Pulse width $P_W \le 1 \ \mu s$, 300 pps
- Note 2: Exponential waveform pulse width $P_W \leq$ 0.2 $\mu s,\,f \leq$ 15 kHz, V_{CC2} = 15 V
- Note 3: For the effective lead soldering area.
- Note 4: This device considered a two-terminal device: All pins on the LED side are shorted together, and all pin on the photodetector side are shorted together.

Recommended Operating Conditions (Note)

Characteristics	Symbol	Min	Тур.	Max	Unit
Total output supply voltage (Note 1)	(VCC2-VEE)	15	-	30	V
Negative output supply voltage	(VE-VEE)	0	-	15	V
Positive output supply voltage	(V _{CC2} -V _E)	15	-	30 - (V _E -V _{EE})	V
Positive input supply voltage	Vcc1	3.3	-	5.5	V
Input on-state current (Note 2)	IF(ON)	7.5	-	10	mA
Input off-state voltage	VF(OFF)	0	-	0.8	V
Operating frequency (Note 3)	f	-	-	50	kHz

Note: Recommended operating conditions are given as a design guideline to obtain expected performance of the device. Additionally, each item is an independent guideline respectively. In developing designs using this product, please confirm specified characteristics shown in this document.

Note 1: If the V_{CC2} rise slope is sharp, an internal circuit might not operate with stability. Please design the V_{CC2} rise slope under 3.0 V / μ s.

Note 2: Input signal rise time (fall time) $\leq 0.5 \ \mu s$.

Note 3: Exponential waveform. I_{OPH} \geq -4.0 A (\leq 90 ns), I_{OPL} \leq 4.0 A (\leq 90 ns), Ta = 110 °C

Electrical Characteristics (Note) (Unless otherwise specified, Ta = -40 to 110 °C, Vcc2 - VEE = 15 to 30 V, VE - VEE = 0 V)

Characteristics	Symbol	Test Circuit	Test Condition	Min	Тур.	Max	Unit	
Input forward voltage	VF	_	IF = 10 mA, Ta = 25°C	1.4 -		1.7	V	
Input reverse current	IR	_	VR = 5 V	-	-	10	μA	
Input capacitance	Ct	_	V = 0 V, f = 1 MHz, Ta = 25 °C	-	95	-	pF	
			IFAULT = 1.1 mA, VCC1 = 5.5 V	-	0.2	0.4		
FAULT low level output voltage	VFAULTL	_	IFAULT = 1.1 mA, VCC1 = 3.3 V	-	0.2	0.4	V	
	1		VFAULT = 5.5 V, VCC1 = 5.5 V, Ta = 25 °C	-	-	0.5		
FAULT high level output current	IFAULTH	_	VFAULT = 5.5 V, VCC1 = 3.3 V, Ta = 25 °C	-	-	0.3	μA	
Lieblevel evter terment (Nete 1)	lanu	4	Vo = Vcc2 - 4 V	-	-4.0	-1.2		
High level output current (Note 1)	Іорн	1	Vo = Vcc2 - 7 V	-	-6.5	-3.0	- A	
Low lovel entrut entrut (Nets 4)	lanı	2	Vo = VEE + 2.5 V	1.2	3.5	-		
Low level output current (Note 1)	IOPL		VO = VEE + 7 V	3	5.5	-		
Low level output current during fault condition	IOLF	_	Vo - Vee = 14 V	90	150	230	mA	
High level output voltage	Vон	3	IO = -100 mA	Vcc2-0.3	VCC2-0.1	-		
Low level output voltage	Vol	4	IO = 100 mA	-	- 0.1	0.2	v	
Clamp pin threshold voltage	VtClamp		_	-	2.5	-		
Clamp low level sinking current	ICL		Vo = VEE + 2.5 V	0.56	1.8	-	А	
High level supply current	Ісс2н	5	IO = 0 mA	-	2.4	3.8		
Low level supply current	ICC2L	6	IO = 0 mA	-	2.3	3.8		
Blanking capacitor charging current	ICHG	7	VDESAT = 2 V	-0.33	-0.24	-0.13	mA	
Blanking capacitor discharge current	IDSCHG	8	VDESAT = 7 V	10	49	-		
DESAT threshold voltage	VDESAT	—	VCC2 - VE > VUVLO-	5.9	6.5	7.5		
	Vuvlo ⁺	9	$V_{0} > 5 V$	10.5	11.6	13.5		
UVLO threshold voltage	Vuvlo ⁻	9	$V_0 < 5 V$	9.2	10.3	11.1	- V	
UVLO hysteresis	UVLO _{HYS}	_	-	-	1.3	-		
Threshold input current (L/H)	IFLH	10	VCC2 = 30 V, VO < 5 V	-	2.6	6	mA	
Threshold input voltage (H/L)	VFHL	_	VCC2 = 30 V, VO > 5 V	0.8	-	-	V	

Note: All typical values are at Ta = 25 $^\circ\text{C}$

Note: This product is more sensitive than conventional products to electrostatic discharge ESD owing to its low power consumption design.

It is therefore all the more necessary to observe general precautions regarding ESD when handling this component.

Note 1: I₀ application time \leq 50 µs, 1 pulse

Isolation Characteristics (Note) (Ta = 25 °C)

Characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit
Capacitance input to output	CS	Vs = 0 V, f = 1 MHz	-	1.0	-	pF
Isolation resistance	Rs	R.H. ≤ 60 %, V _S = 500 V	10 ¹²	10 ¹⁴	-	Ω
Isolation voltage	BVs	AC, 60 s	5000	-		Vrms

Note: This device considered a two-terminal device: All pins on the LED side are shorted together, and all pin on the photodetector side are shorted together.

Switching Characteristics (Note) (Unless otherwise specified, Ta = -40 to 110 °C, Vcc2 - V EE = 15 to 30 V, VE - VEE = 0 V)

Characteristics		Symbol	Test Circuit	Test C	Condition	Min	Тур.	Max	Unit
Propagation delay time	$L\toH$	tрLH			$I_F=0 \rightarrow 10 \text{ mA}$	50	85	150	
(Note 1)	$H\toL$	tpHL			$I_F = 10 \rightarrow 0 \text{ mA}$	50	90	150	
Output rise time (10-90 %)	(Note 1)	tr		$R_g = 10 \Omega$,	$I_F = 0 \rightarrow 10 \text{ mA}$	-	32	-	
Output fall time (90-10 %)	(Note 1)	tf	11	$C_{g} = 25 \text{ nF},$	$I_F = 10 \rightarrow 0 \text{ mA}$	-	18	-	ns
Pulse with distortion ((Note 1)	tрнL-tрLH		V _{CC2} = 30 V	$I_F = 0 \leftrightarrow 10 \text{ mA}$	-	-	50	
	(Note 1) (Note 2)	tpsk			$I_F = 0 \leftrightarrow 10 \text{ mA}$	-80	-	80	
DESAT sense to 90% delay	y	tdesat(90%)			Cg = 25 nF	-	230	500	
DESAT sense to 10% delay	N.	tdesat(10%)			Cg = 25 nF	-	7.0	8.5	
	y			$\label{eq:cdesat} \begin{array}{l} {C_{DESAT}=100 \ pF,} \\ {R_{g}=10 \ \Omega,} \\ {V_{CC2}=30 \ V,} \\ {R_{F}=2.1 \ k\Omega,} \\ {V_{CC1}=5 \ V} \end{array}$	Cg = 10 nF	-	2.5	3.5	μS
DESAT leading edge blanki	ing time	tdesat(leb)				-	1.1	-	
DESAT filter time		tdesat(filter)				-	90	-	ns
DESAT sense to low level FAULT signal delay		tDESAT(FAULT)	12			-	350	550	ns
DESAT sense to low propaged delay	gation	tDESAT(LOW)				-	200	-	115
DESAT input mute		tdesat(mute)				7	20	-	
RESET to high level FAULT signal delay	Г	treset(fault)		$\begin{array}{l} C_{DESAT} = 100 \ p\text{F}, \\ Rg = 10 \ \Omega, \\ V_{CC2} = 30 \ V, \\ R\text{F} = 2.1 \ k\Omega, \\ V_{CC1} = 5.5 \ V \end{array}$		0.2	0.6	2	μs
High-level Common-mode transient immunity	(Note 3)	CMH		T _a = 25 °C, Rg = 10 Ω,	V _{O (min)} = 26 V, VFAULT(min) = 2 V	±35	-	-	
Low-level Common-mode transient immunity	(Note 4)	CML	$\begin{array}{c} Cg = 25 \text{ nF}, \\ 13 \text{ to} \\ 16 \\ V_{CC2} = 30 \text{ V}, \\ D_{T} = 24 \text{ kC} \end{array}$	Vo (max) = 1 V, VFAULT(max) = 0.8 V	±35	-	-	kV/μs	

Note: All typical values are at $T_a = 25$ °C.

Note 1: Input signal (f = 10 kHz, duty = 50%, tr = tf = 5 ns or less)

C_L is approximately 15 pF which includes probe and stray wiring capacitance.

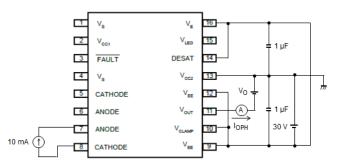
Note 2: The propagation delay skew, t_{psk}, is equal to the magnitude of the worst-case difference in t_{pHL} and/or t_{pLH} that will be seen between units at the same given conditions (supply voltage, input current, temperature, etc).

Note 3: CM_H is the maximum rate of fall of the common mode voltage that can sustained with the output voltage in the logic high state ($V_O > 26$ V or $V_{FAULT} > 2$ V).

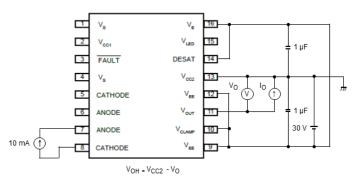
Note 4: CM_L is the maximum rate of rise of the common mode voltage that can sustained with the output voltage in the logic low state ($V_O < 1$ V or $V_{FAULT} < 0.8$ V).

Test Circuit

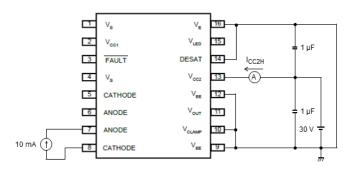




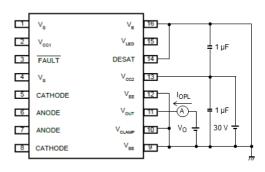
Test Circuit 3: VOH



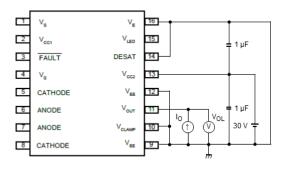
Test Circuit 5: ICC2H



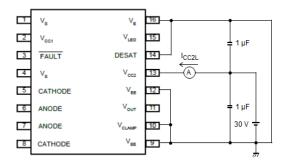
Test Circuit 2: IOPL



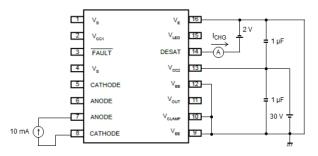
Test Circuit 4: VoL



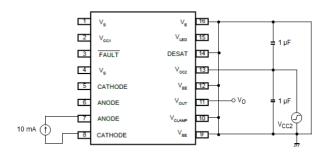
Test Circuit 6: ICC2L



Test Circuit 7: ICHG

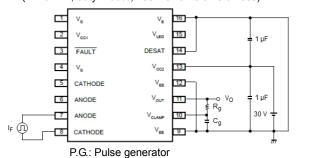


Test Circuit 9: VUVLO

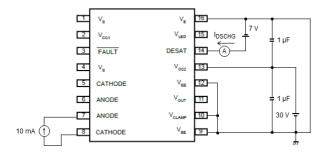


Test Circuit 11: tpLH, tpHL, tr, tf, | tpHL-tpLH |

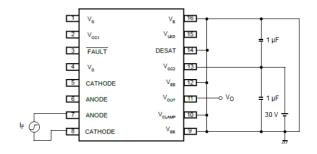
IF = 10 mA (P.G.) (f =10 kHz, duty = 50%, rise / fall time 5 ns or less)

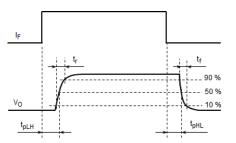


Test Circuit 8: IDSCHG



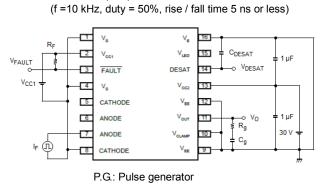
Test Circuit 10: IFLH

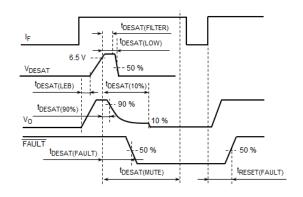




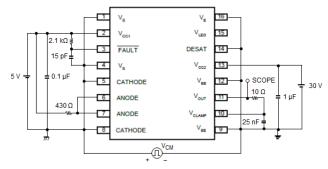
Test Circuit 12: tdesat(90%), tdesat(10%), tdesat(leb), tdesat(filter), tdesat(fault), tdesat(low), tdesat(mute), treset(fault)

IF = 10 mA (P.G.)

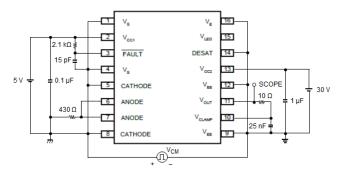




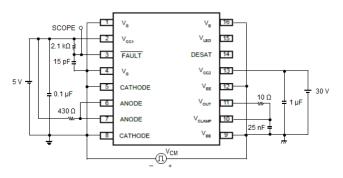
Test Circuit 13: CMR_LED1 ON



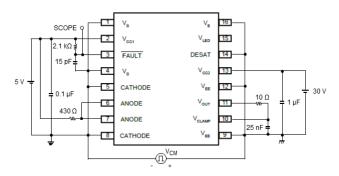
Test Circuit 14: CMR_LED1 OFF



Test Circuit 15: CMR_LED2 ON

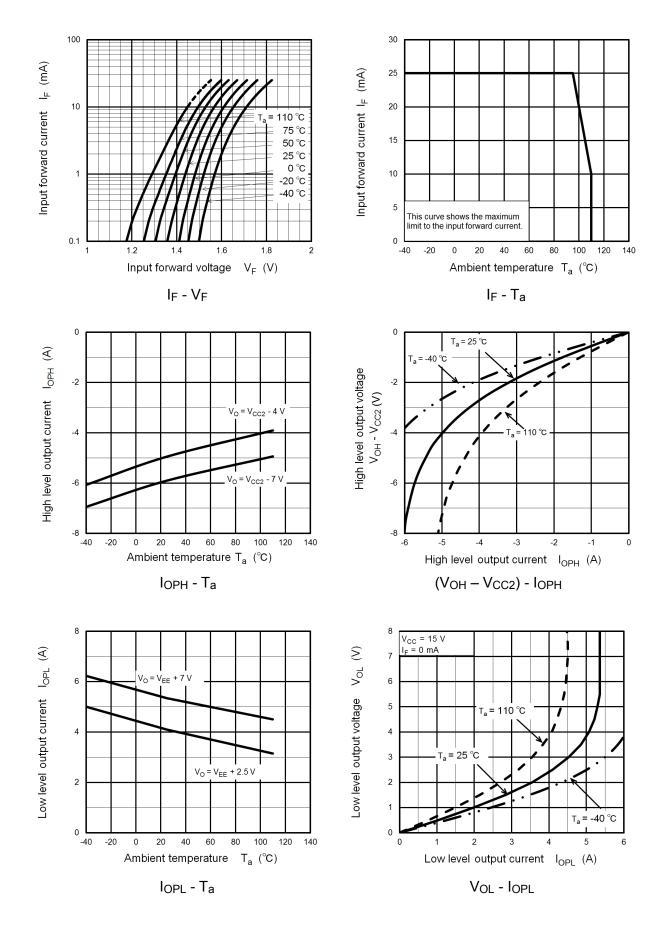


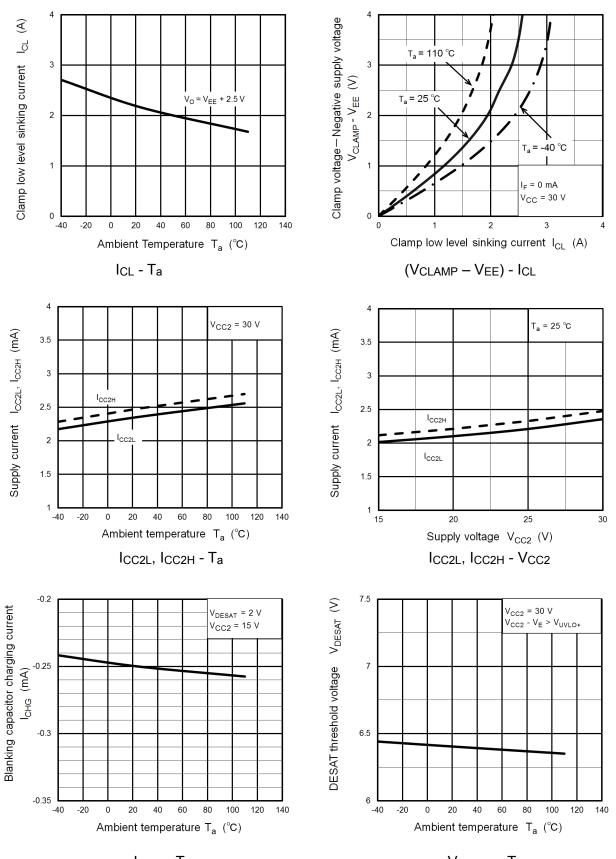
Test Circuit 16: CMR_LED2 OFF



Characteristics Curves (Note)

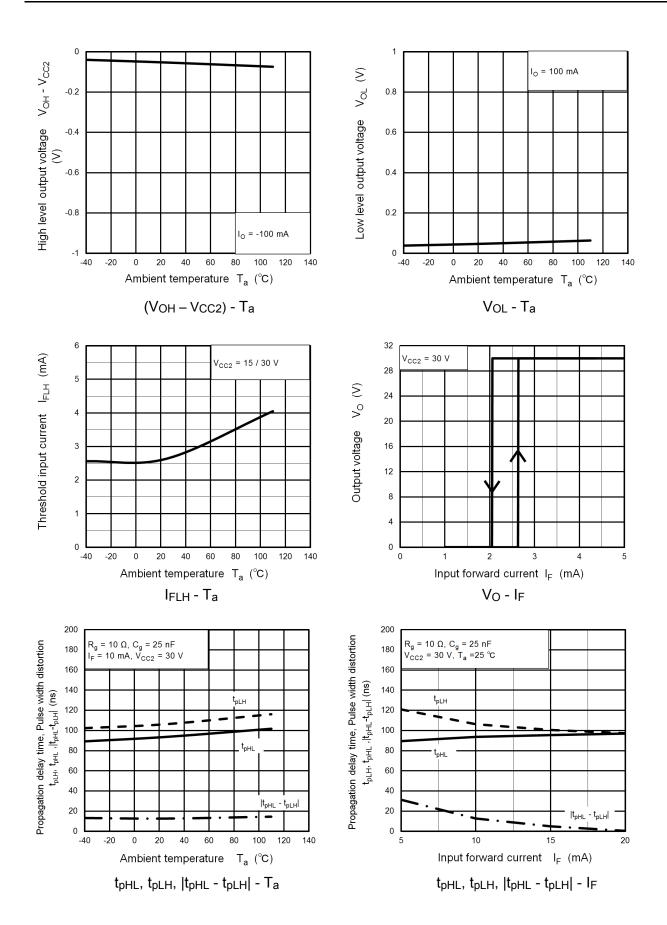
TOSHIBA

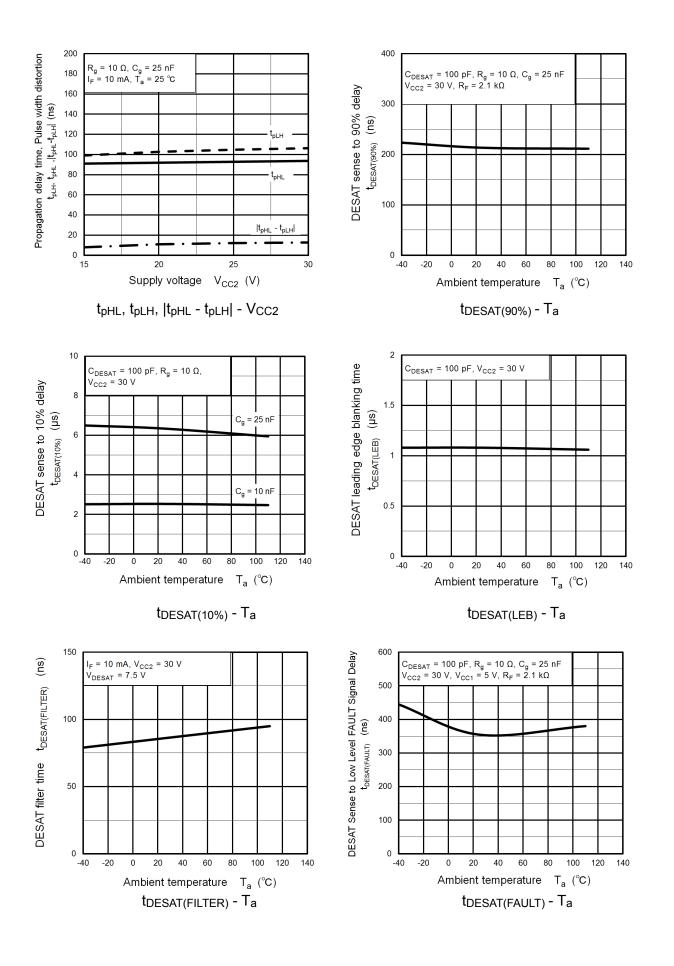


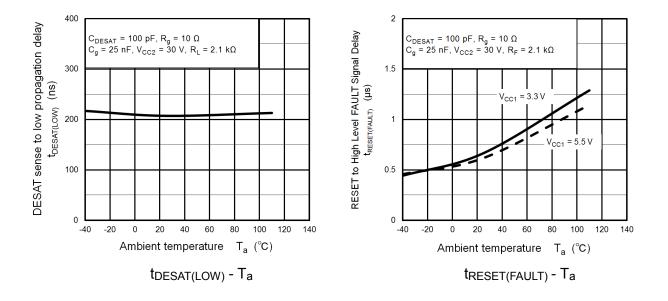


I_{CHG} - Та

V_{DESAT} - T_a







Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Soldering and Storage

(1) Precautions for Soldering

The soldering temperature should be controlled as closely as possible to the conditions shown below, irrespective of whether a soldering iron or a reflow soldering method is used.

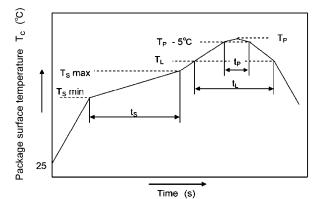
· When using soldering reflow

The soldering temperature profile is based on the package surface temperature.

(See the figure shown below, which is based on the package surface temperature.)

Reflow soldering must be performed once or twice.

The mounting should be complicated with the interval from the first to the last mountings being 2 weeks.



	Symbol	Min	Max	Unit
Preheat temperature	Ts	150	200	°C
Preheat time	ts	60	120	s
Ramp-up rate $(T_L \text{ to } T_P)$			3	°C/s
Liquidus temperature	TL	2	°C	
Time above T_L	tL	60	150	S
Peak temperature	Τ _Ρ		260	°C
Time during which T_c is between ($T_P - 5$) and T_P	t _P		30	s
Ramp-down rate $(T_P \text{ to } T_L)$			6	°C/s

An example of a temperature profile when lead(Pb)-free solder is used

· When using soldering flow

Preheat the device at a temperature of 150 °C (package surface temperature) for 60 to 150 seconds. Mounting condition of 260 °C within 10 seconds is recommended. Flow soldering must be performed once.

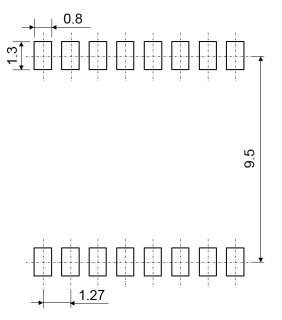
 When using soldering iron Complete soldering within 10 seconds for lead temperature not exceeding 260 °C or within 3 seconds not exceeding 350 °C.

Heating by soldering iron must be done only once per lead.

(2) Precautions for General Storage

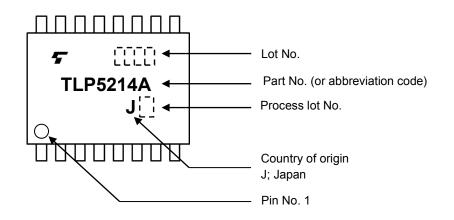
- · Avoid storage locations where devices may be exposed to moisture or direct sunlight.
- · Follow the precautions printed on the packing label of the device for transportation and storage.
- Keep the storage location temperature and humidity within a range of 5 °C to 35 °C and 45 % to 75 %.
- Do not store the products in locations with poisonous gases (especially corrosive gases) or in dusty conditions.
- Store the products in locations with minimal temperature fluctuations. Rapid temperature changes during storage can cause condensation, resulting in lead oxidation of corrosion, which will deteriorate the solderability of the leads.
- · When restoring devices after removal from their packing, use anti-static containers.
- · Do not allow loads to be applied directly to devices while they are in storage.
- If devices have been stored for more than two years under normal storage conditions, it is recommended that you check the leads for ease of soldering prior to use.

Land Pattern Dimensions for Reference Only



Unit: mm

Marking



1. Ordering Method

When placing an order, please specify the part number, the tape and the quantity (Multiples of 1500) as shown in the following example.

Example) TLP5214A(TP,E 1500 pcs

Part number: TLP5214A Tape type: TP (12-mm pitch) [[G]]/RoHS COMPATIBLE: E (Note 1) Quantity (must be a multiple of 1500): 1500 pcs

Note 1 :Please contact your Toshiba sales representative for details on environmental information such as the product's RoHS compatibility.

RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

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